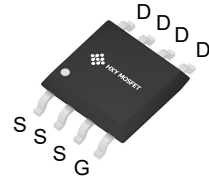




Description

The CWDM3011P uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOP-8
(SOIC-8)

General Features

$V_{DS} = -30V$ $I_D = -11A$

$R_{DS(ON)} < 16m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
CWDM3011P	SOP-8(SOIC-8)	HXY MOSFET	3000

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	- 30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ C$	Drain Current , V_{GS} @ 10V	-11	A
IDM	Pulsed Drain Current	-40	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	3.7	W
TSTG	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction-ambient	33.8	°C/W



Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D = -250\mu A$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS}=0V,$	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}= \pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D = -250\mu A$	-1.0	-1.6	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance Note3	$V_{GS} = -10V, I_D = -10A$	-	13	16	m Ω
		$V_{GS} = -4.5V, I_D = -5A$	-	18	27	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = -15V, V_{GS}=0V,$ $f=1.0MHz$	-	1330	-	pF
C_{oss}	Output Capacitance		-	183	-	pF
C_{rss}	Reverse Transfer Capacitance		-	156	-	pF
Q_g	Total Gate Charge	$V_{DS} = -15V, I_D = -5A,$ $V_{GS} = -10V$	-	22	-	nC
Q_{gs}	Gate-Source Charge		-	1.0	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	1.8	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = -15V, I_D = -10A,$ $V_{GS} = -10V, R_{GEN} = 2.5\Omega$	-	9	-	ns
t_r	Turn-on Rise Time		-	13	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	48	-	ns
t_f	Turn-off Fall Time		-	20	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-11	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-40	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S = -15A$	-	-0.8	-1.2	V
t_{rr}	Reverse Recovery Time	$T_J=25^\circ\text{C},$	-	64	-	ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = -24V, I_F = -2.8A,$ $di/dt = -100A/\mu s$	-	25	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^\circ\text{C}, V_{GS}=10V, R_G=25\Omega, L=0.5mH, I_{AS}=-12.7A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$



Typical Characteristics

Figure 1: Output Characteristics



Figure 2: Typical Transfer Characteristics

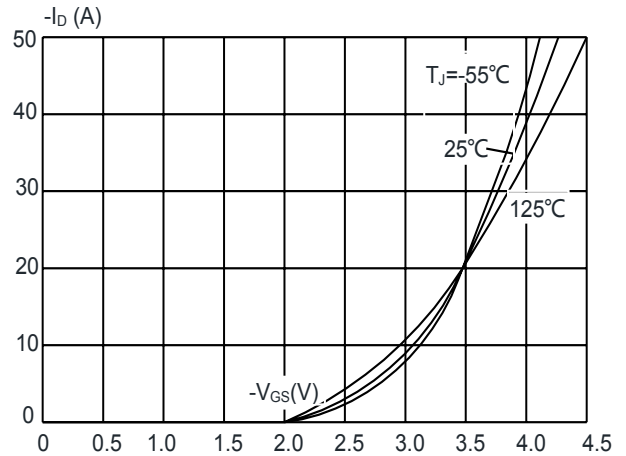


Figure 3: On-resistance vs. Drain Current



Figure 4: Body Diode Characteristics

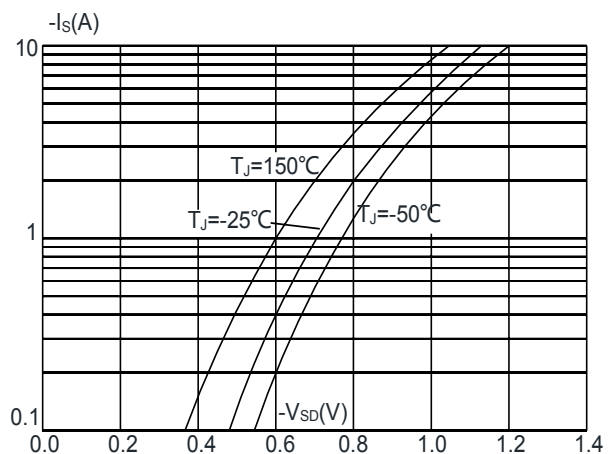


Figure 5: Gate Charge Characteristics



Figure 6: Capacitance Characteristics

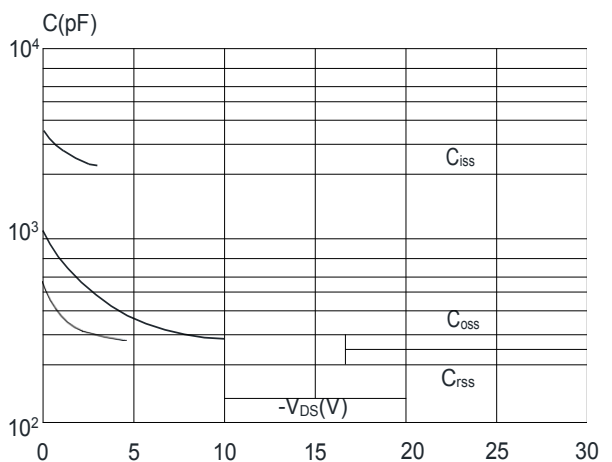




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

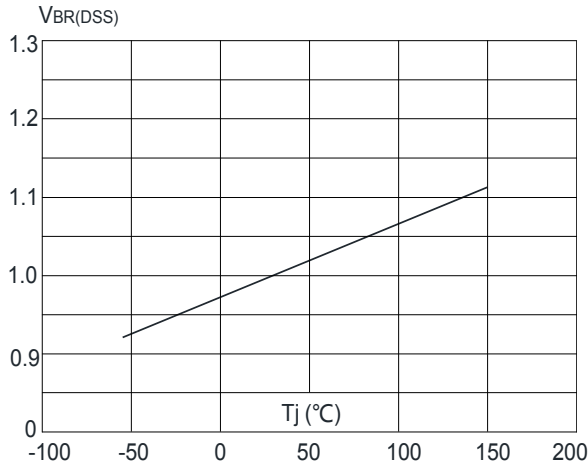


Figure 8: Normalized on Resistance vs. Junction Temperature

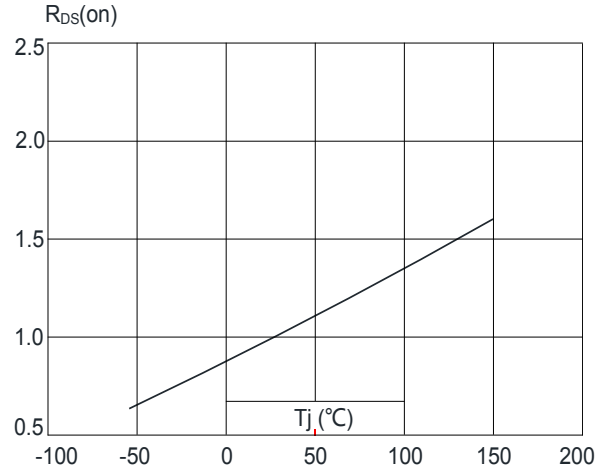


Figure 9: Maximum Safe Operating Area

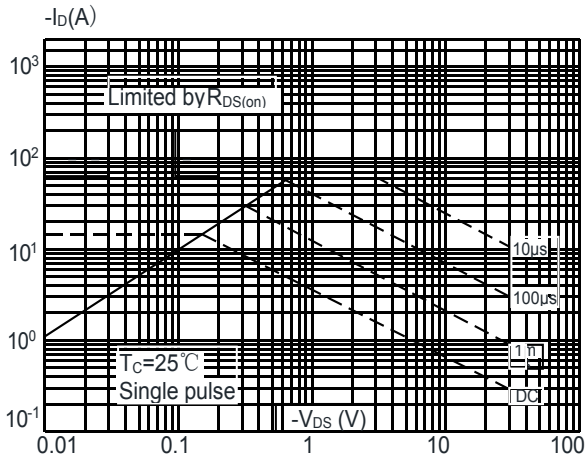


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

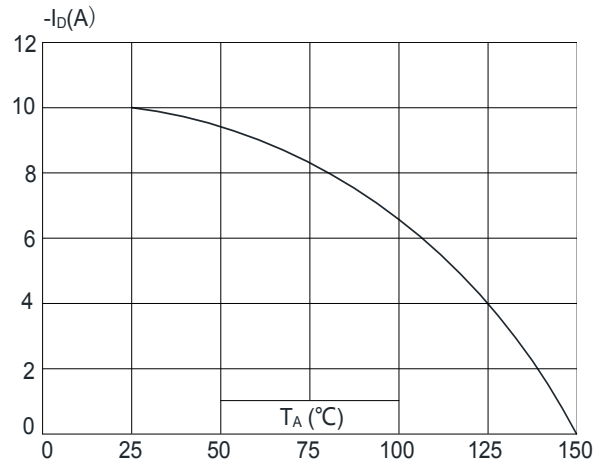
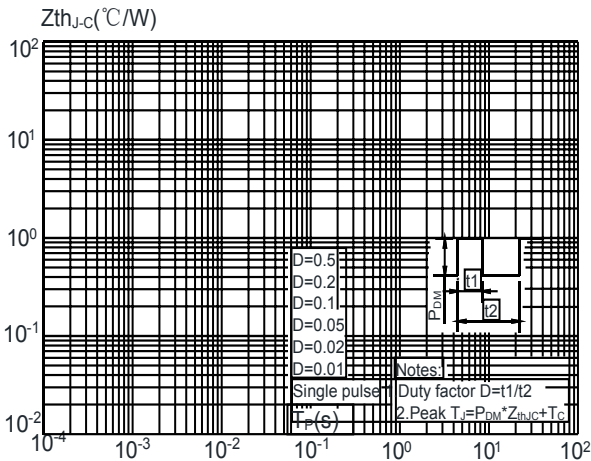


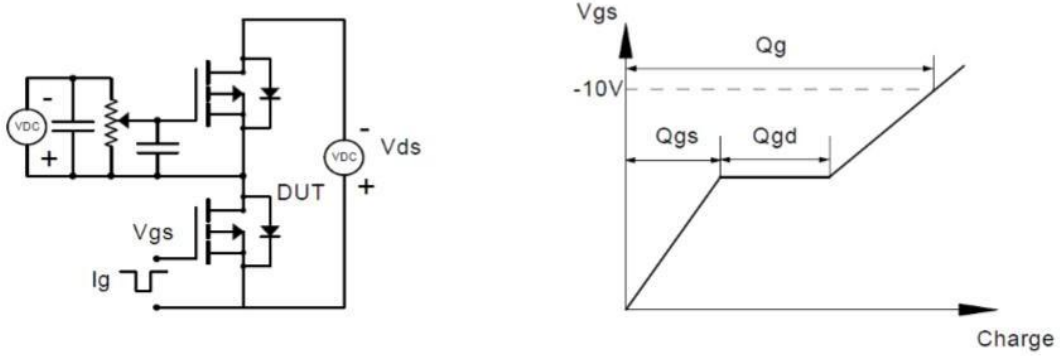
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



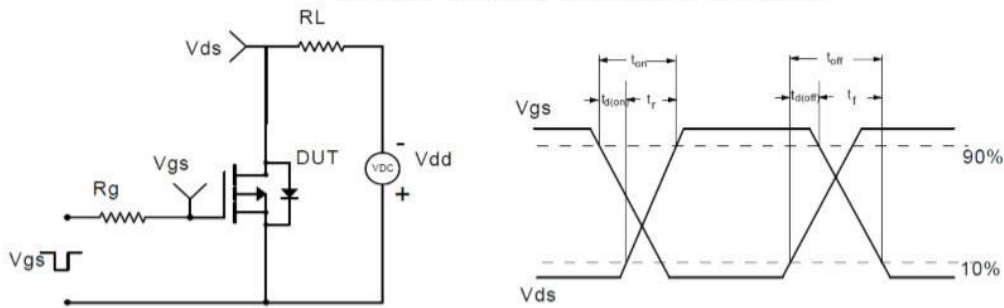


Test Circuit

Gate Charge Test Circuit & Waveform



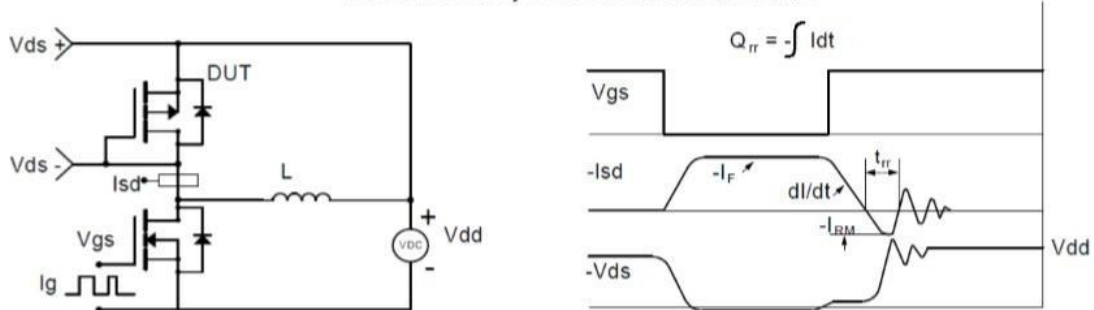
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

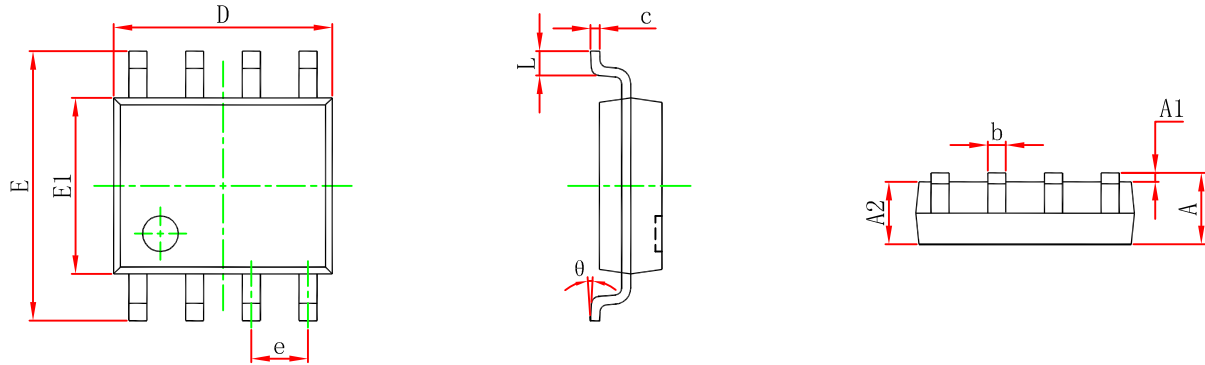


Diode Recovery Test Circuit & Waveforms

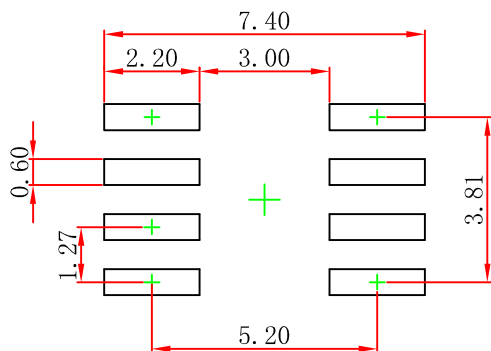




SOP-8(SOIC-8) Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270(BSC)		0.050(BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.



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